		0 1 m	DB	Time stamp
L Number	Hits	Search Text semiconductor and plug and (antifuse)	USPAT;	2003/01/13 15:43
-	157	semiconductor and plug and (antiluse)	US-PGPUB;	2000,01,10 10110
+			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	487	semiconductor and interconnect and	USPAT;	2003/01/14 12:08
		(antifuse)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	205	(semiconductor and interconnect and	USPAT;	2003/01/14 14:50
-	203	(antifuse)) and (sidewall or barrier)	US-PGPUB;	
		(diffiluse)) and (sidewall of balliot)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
			USPAT;	2003/01/14 14:53
-	26	,		2003/01/14 14:33
		(antifuse)) and (SiN)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	(semiconductor and interconnect and	USPAT;	2003/01/14 14:54
	J	(antifuse)) and (silicon with nitrde)	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
1	100	(semiconductor and interconnect and	USPAT;	2003/01/14 14:54
-	180	(Semiconductor and Interconnect and	US-PGPUB;	-555, 52, 21 21.51
		(antifuse)) and (silicon with nitride)	EPO; JPO;	
1				
			DERWENT;	
			IBM_TDB	0000 /01 /14 14 54
-	154	((semiconductor and interconnect and	USPAT;	2003/01/14 14:54
		(antifuse)) and (silicon with nitride))	US-PGPUB;	
		not ((semiconductor and interconnect and	EPO; JPO;	
		(antifuse)) and (SiN))	DERWENT;	
		(difference) and (servi)	IBM TDB	
	40	(ESD with protection) and antifuse	USPAT;	2003/01/15 15:43
-	40	(ESD with protection, and antirase	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
1				2003/01/15 15:45
1 -	1	1 ,	USPAT;	2003/01/13 13.43
		trench\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
1_	2	("6396120").PN.	USPAT;	2003/01/15 15:50
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
		(HAA7CA70H HE1CCEECH HE0CO4EOH	USPAT	2003/01/15 15:46
1 -	13		OSEMI	2003,01,13 13.40
		"5304508" "5314840" "5469109"		
		"5485032" "5572062" "5672994"		
		"5774011" "5804500" "5811870"		
		"5904507").PN.		0000/01/05 55 55
_	2	("6458631").PN.	USPAT;	2003/01/15 15:51
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	İ
	_	("6440850").PN.	USPAT;	2003/01/15 15:55
-	2	(0440030).FN.	US-PGPUB;	,,
1			EPO; JPO;	
			DERWENT;	1
1			IBM_TDB	
	2	("6335228").PN.	USPAT;	2003/01/15 15:55
_	2	,	Luc Berun.	I
-	2		US-PGPUB;	į
-	2		EPO; JPO;	
_	2			

Search History 1/25/03 12:16:18 AM Page 1

6	("5904507" "6081021" "6087677"	USPAT	2003/01/15 16:22
5	"6097077" "6124194" "6335228").PN. semiconductor and antifuse and BPSG and "p-type" and "n-type" and (doped with	USPAT; US-PGPUB;	2003/01/21 10:13
9	semiconductor and antifuse and BPSG and "p-type" and "n-type"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/21 10:13
4	"p-type" and "n-type") not (semiconductor and antifuse and BPSG and "p-type" and	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 10:42
2817	semiconductor and plug\$1 and "p-type" and "n-type"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/21 10:43
767	(semiconductor and plug\$1 and "p-type" and "n-type") and BPSG	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/21 10:43
267	((semiconductor and plug\$1 and "p-type" and "n-type") and BPSG) and (copper or Cu)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 14:02
154	semiconductor and antifuse and "p-type" and "n-type"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 14:56
73	semiconductor and antifuse and BPSG	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 15:03
203	semiconductor and antifuse and (copper or cu)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 15:04
66	(semiconductor and antifuse and (copper or cu)) and (doped with silicon)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 15:17
52	semiconductor and plug and (barrier with SiON)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 15:23
1	(semiconductor and plug and (barrier with SiON)) and (doped with silicon with plug)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 15:24
2	(semiconductor and plug and (barrier with SiON)) and (doped with silicon with conductive)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/21 15:24
	5 9 9 4 4 2817 767 267 154 73 203 66 52 1	semiconductor and antifuse and BPSG and "p-type" and "n-type") not (semiconductor and antifuse and BPSG and "p-type" and "n-type") not (semiconductor and antifuse and BPSG and "p-type" and "n-type") not (semiconductor and antifuse and BPSG and "p-type" and "n-type" and (doped with silicon)) 2817 semiconductor and plug\$1 and "p-type" and "n-type" 767 (semiconductor and plug\$1 and "p-type" and "n-type") and BPSG 267 ((semiconductor and plug\$1 and "p-type" and "n-type") and BPSG) and (copper or Cu) 154 semiconductor and antifuse and "p-type" and "n-type" 73 semiconductor and antifuse and BPSG 203 semiconductor and antifuse and (copper or cu) 66 (semiconductor and antifuse and (copper or cu)) and (doped with silicon) 52 semiconductor and plug and (barrier with siON)) and (doped with silicon with plug) 2 (semiconductor and plug and (barrier with siON)) and (doped with silicon with	semiconductor and antifuse and BPSG and "p-type" and "n-type" of and antifuse and BPSG and "p-type" and "n-type" of and antifuse and BPSG and "p-type" and "n-type" of and antifuse and BPSG and "p-type" and "n-type" of and antifuse and BPSG and "p-type" and "n-type" of and antifuse and BPSG and "p-type" and antifuse and BPSG and "p-type" and "n-type" of and antifuse and BPSG and "n-type" and (doped with silicon) of antifuse and BPSG and "n-type" and "n-type" of and "n-type"